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N-channel TrenchMOS logic level FET Rev. 3 — 19 April 2011

Product data sheet

Product profile 1.

1.1 General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

1.2 Features and benefits

AEC Q101 compliant

Low conduction losses due to low on-state resistance

1.3 Applications

Automotive and general purpose power switching

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	100	V
I _D	drain current	T _{mb} = 25 °C	-	-	75	А
P _{tot}	total power dissipation		-	-	230	W
Т _ј	junction temperature		-55	-	175	°C
Static cha	racteristics					
R _{DSon}	R _{DSon} drain-source on-state resistance	$\label{eq:VGS} \begin{array}{l} V_{GS} = 10 \; V; \; I_{D} = 25 \; A; \\ T_{j} = 25 \; ^{\circ} C \end{array}$	-	11.5	14.4	mΩ
		$\label{eq:VGS} \begin{array}{l} V_{GS} = 5 \ V; \ I_{D} = 25 \ A; \\ T_{j} = 25 \ ^{\circ}C \end{array}$	- 12	15	mΩ	
Avalanche	e ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$ \begin{split} I_D &= 35 \text{ A}; \ V_{sup} \leq 25 \text{ V}; \\ R_{GS} &= 50 \ \Omega; \ V_{GS} = 5 \text{ V}; \\ T_{j(\text{init})} &= 25 \ ^\circ\text{C}; \ \text{unclamped} \end{split} $	-	-	120	mJ



N-channel TrenchMOS logic level FET

2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain	mb	
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT78A (TO-220AB)	

3. Ordering information

Table 3.Ordering information

Type number	Package		
	Name	Description	Version
BUK9515-100A	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78A

4. Limiting values

Table 4.Limiting values

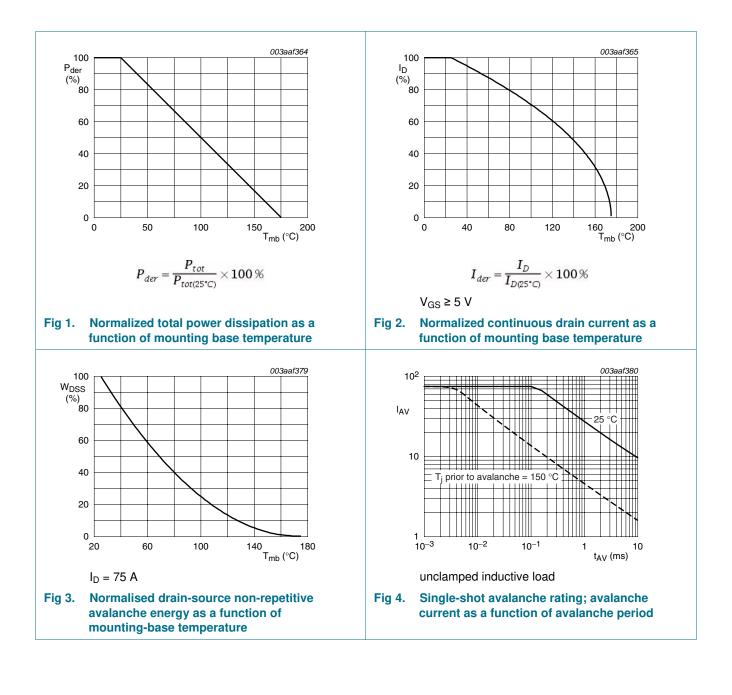
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	100	V
V _{DGR}	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$	-	100	V
V _{GS}	gate-source voltage		-10	10	V
I _D	drain current	T _{mb} = 25 °C	-	75	А
		$T_{mb} = 100 \ ^{\circ}C$	-	53	А
I _{DM}	peak drain current	T _{mb} = 25 °C; pulsed	-	313	А
P _{tot}	total power dissipation	T _{mb} = 25 °C	-	230	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
V _{GSM}	peak gate-source voltage	pulsed; t _p ≤ 50 μs	-15	15	V
Source-drai	in diode				
I _S	source current	T _{mb} = 25 °C	-	75	А
I _{SM}	peak source current	pulsed; T _{mb} = 25 °C	-	313	А
Avalanche i	ruggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$\label{eq:ID} \begin{array}{l} I_D = 35 \text{ A}; \ V_{sup} \leq 25 \text{ V}; \ R_{GS} = 50 \ \Omega; \\ V_{GS} = 5 \text{ V}; \ T_{j(init)} = 25 \ ^{\circ}\text{C}; \ unclamped \end{array}$	-	120	mJ
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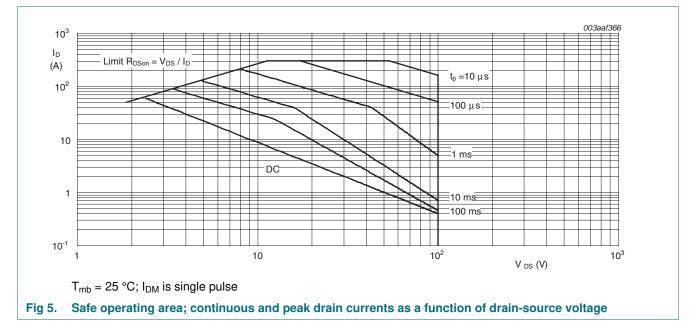
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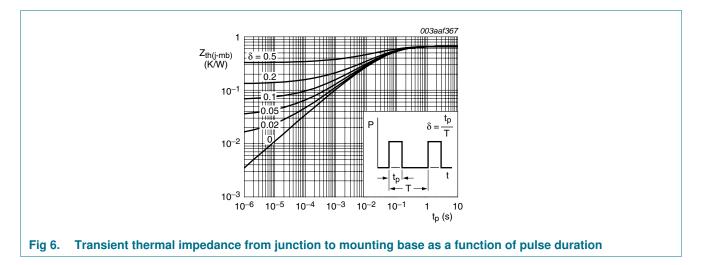
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5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base		-	-	0.65	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	-	60	-	K/W

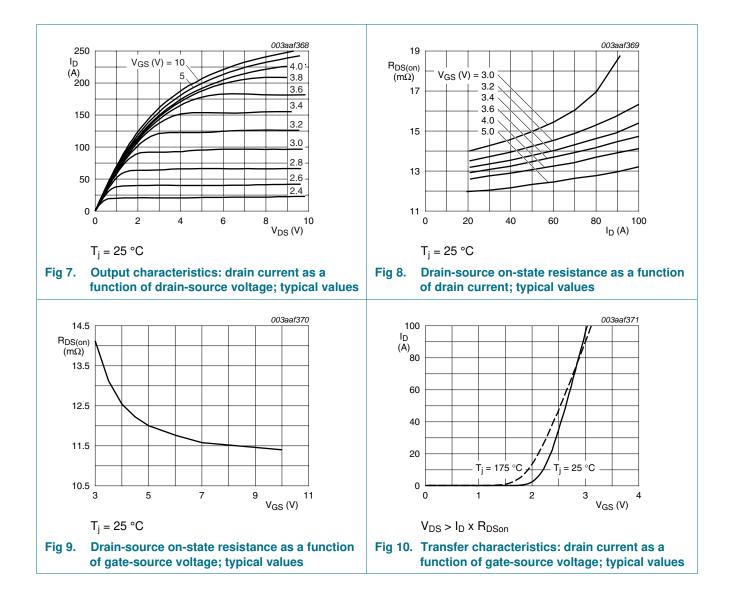


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6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V _{(BR)DSS}	drain-source	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	100	-	-	V
	breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	89	-	-	V
V _{GS(th)}	gate-source threshold	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	1	1.5	2	V
	voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}$	-	-	2.3	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C}$	0.5	-	-	V
I _{DSS}	drain leakage current	V_{DS} = 100 V; V_{GS} = 0 V; T_j = 175 °C	-	-	500	μA
		V_{DS} = 100 V; V_{GS} = 0 V; T_j = 25 °C	-	0.05	10	μA
I _{GSS}	gate leakage current	V_{GS} = 10 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
		V_{GS} = -10 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state	$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C}$	-	-	16	mΩ
	resistance	V _{GS} = 5 V; I _D = 25 A; T _j = 175 °C	-	-	40.5	mΩ
		V_{GS} = 10 V; I _D = 25 A; T _j = 25 °C	-	11.5	14.4	mΩ
		$V_{GS} = 5 \text{ V}; \text{ I}_{D} = 25 \text{ A}; \text{ T}_{j} = 25 \text{ °C}$	-	12	15	mΩ
Dynamic	characteristics					
C _{iss}	input capacitance	$V_{GS} = 0$ V; $V_{DS} = 25$ V; f = 1 MHz;	-	6500	8600	pF
C _{oss}	output capacitance	$T_j = 25 \ ^{\circ}C$	-	550	660	pF
C _{rss}	reverse transfer capacitance		-	325	400	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 30 \text{ V}; \text{ R}_{L} = 1.2 \Omega; \text{ V}_{GS} = 5 \text{ V};$	-	45	65	ns
t _r	rise time	$R_{G(ext)} = 10 \ \Omega; \ T_j = 25 \ ^{\circ}C$	-	130	195	ns
t _{d(off)}	turn-off delay time		-	400	560	ns
t _f	fall time		-	130	190	ns
L _D	internal drain inductance	measured from contact screw on mounting base to centre of die; $T_j = 25 \text{ °C}$	-	3.5	-	nH
		measured from drain lead 6 mm from package to centre of die; $T_j = 25 \text{ °C}$	-	4.5	-	nH
L _S	internal source inductance	measured from source lead to source bond pad; $T_j = 25 \text{ °C}$	-	7.5	-	nH
Source-d	rain diode					
V _{SD}	source-drain voltage	$I_{S} = 75 \text{ A}; V_{GS} = 0 \text{ V}; T_{j} = 25 \text{ °C}$	-	1.1	-	V
		I _S = 25 A; V _{GS} = 0 V; T _j = 25 °C	-	0.85	1.2	V
t _{rr}	reverse recovery time	I _S = 75 A; dI _S /dt = -100 A/μs;	-	60	-	ns
Q _r	recovered charge	V _{GS} = -10 V; V _{DS} = 30 V; T _j = 25 °C		0.24		μC

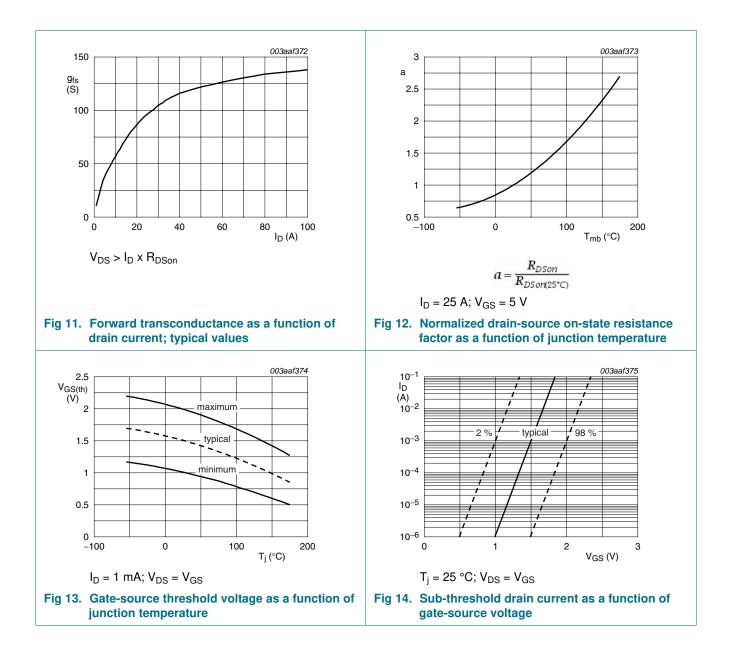
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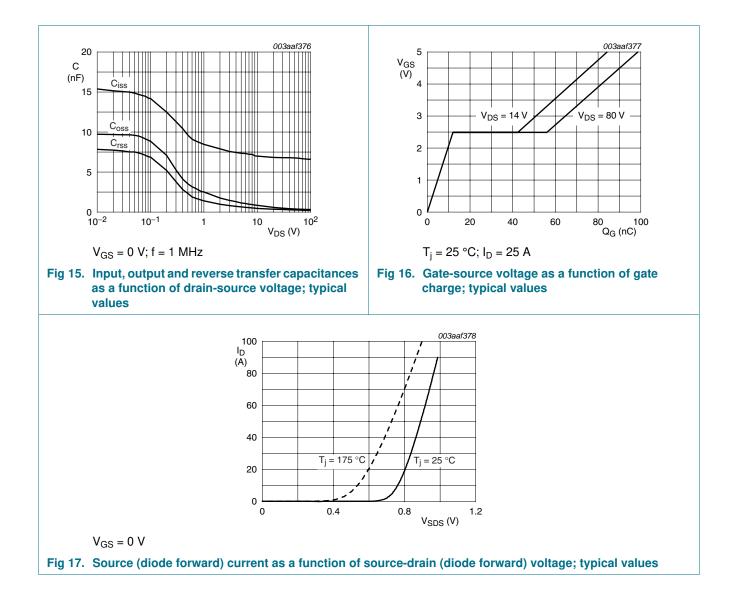
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7. Package outline

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	4.5	A ₁ 1.39	0.9	V1 1.3	с 0.7	15.8	6.4	10.3		L 15.0	-1 ⁽¹⁾ 3.30	max.	р 3.8	q 3.0	2.6	-
mm	4.1	1.27	0.6	1.0	0.4	15.2	5.9	9.7	2.54	13.5	2.79	3.0	3.6	2.7	2.2	
		nis zono	are not t	inned												
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Fig 18. Package outline SOT78A (TO-220AB)

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N-channel TrenchMOS logic level FET

8. Revision history

Release date	Data sheet status	Change notice	Supersedes
20110419	Product data sheet	-	BUK9515_9615-100A_2
		•	comply with the new identity
 Legal texts 	s have been adapted to t	he new company r	name where appropriate.
 Type numl 	ber BUK9515-100A sepa	arated from data sh	neet BUK9515_9615-100A_2.
19991101	Product specification	-	-
	20110419 • The forma guidelines • Legal texts • Type number	 20110419 Product data sheet The format of this data sheet has be guidelines of NXP Semiconductors Legal texts have been adapted to t Type number BUK9515-100A separation 	 20110419 Product data sheet - The format of this data sheet has been redesigned to guidelines of NXP Semiconductors. Legal texts have been adapted to the new company r Type number BUK9515-100A separated from data sh

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9. Legal information

9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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BUK9515-100A

N-channel TrenchMOS logic level FET

11. Contents

1	Product profile1
1.1	General description1
1.2	Features and benefits1
1.3	Applications1
1.4	Quick reference data1
2	Pinning information2
3	Ordering information2
4	Limiting values2
5	Thermal characteristics4
6	Characteristics5
7	Package outline9
8	Revision history10
9	Legal information11
9.1	Data sheet status11
9.2	Definitions11
9.3	Disclaimers
9.4	Trademarks12
10	Contact information12

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